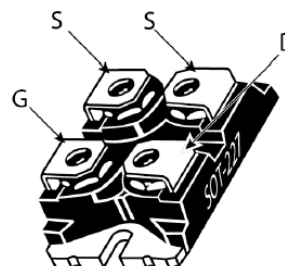


### Description

Silicon Carbide (SiC) MOSFET use a completely new technology that provide superior switching performance and higher reliability compared to Silicon. In addition, the low ON resistance and compact chip size ensure low capacitance and gate charge. Consequently, system benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size.

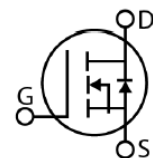
### Features

- High Speed Switching with Low Capacitances
- High Blocking Voltage with Low RDS(on)
- Fast and reliable body diode
- Easy to parallel and simple to drive
- Superior avalanche ruggedness
- ROHS Compliant, Halogen free
- Isolated voltage to 2500 V



### Application

- PV inverter, converter, and industrial motor drives
- Smart grid transmission and distribution
- Induction heating and welding
- Power supply and distribution
- H/EV powertrain and EV charger



G—Gate  
D—Drain  
S—Source

### Ordering Information

| Part Number    | Marking        | Package | Packaging |
|----------------|----------------|---------|-----------|
| A2G100N1200MDS | A2G100N1200MDS | SOT227  | Box       |

**Absolute Maximum Ratings(Tc=25 °C)**

| Symbol                            | Parameter                               | Value       | Unit |
|-----------------------------------|-----------------------------------------|-------------|------|
| V <sub>DS</sub>                   | Drain-Source Voltage                    | 1200        | V    |
| I <sub>D</sub>                    | Drain Current(continuous)at Tc=25°C     | 115         | A    |
| I <sub>D</sub>                    | Drain Current(continuous)at Tc=100°C    | 85          | A    |
| I <sub>DM</sub>                   | Drain Current (pulsed)                  | 280         | A    |
| V <sub>GS</sub>                   | Gate-Source Voltage                     | -10/+25     | V    |
| P <sub>D</sub>                    | Power Dissipation T <sub>c</sub> = 25°C | 428         | W    |
| T <sub>J</sub> , T <sub>stg</sub> | Junction and Storage Temperature Range  | -55 to +175 | °C   |

**Electrical Characteristics(T<sub>J</sub> = 25 °C unless otherwise specified)**
**Typical Performance-Static**

| Symbol               | Parameter                         | Test Conditions                                                      | Min. | Typ. | Max. | Unit |
|----------------------|-----------------------------------|----------------------------------------------------------------------|------|------|------|------|
| BV <sub>DS</sub>     | Drain-source Breakdown Voltage    | I <sub>D</sub> =100uA, V <sub>GS</sub> =0V                           | 1200 |      |      | V    |
| I <sub>DSS</sub>     | Zero Gate Voltage Drain Current   | V <sub>DS</sub> =1200V,<br>V <sub>GS</sub> =0V, T <sub>J</sub> =25°C |      | 5    | 100  | uA   |
| I <sub>GSS</sub>     | Gate-body Leakage Current         | V <sub>DS</sub> =0V ; V <sub>GS</sub> =-10 to 20V                    |      | 10   | 100  | nA   |
| V <sub>GS(th)</sub>  | Gate Threshold Voltage            | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> =22mA             | 2    | 3    | 4    | V    |
| V <sub>GS(on)</sub>  | Recommended turn-on Voltage       | Static                                                               |      | 20   |      | V    |
| V <sub>GS(off)</sub> | Recommended turn-off Voltage      |                                                                      |      | -5   |      | V    |
| R <sub>DS(on)</sub>  | Static Drain-source On Resistance | V <sub>GS</sub> =20V, I <sub>D</sub> =50A                            |      | 16   | 22   | mΩ   |
|                      |                                   | V <sub>GS</sub> =20V, I <sub>D</sub> =50A<br>T <sub>J</sub> =175°C   |      | 32   |      | mΩ   |

**Typical Performance-Dynamic**

| Symbol              | Parameter                      | Test Conditions                                                                                            | Min. | Typ. | Max. | Unit |
|---------------------|--------------------------------|------------------------------------------------------------------------------------------------------------|------|------|------|------|
| C <sub>iss</sub>    | Input Capacitance              | V <sub>DS</sub> =1000V, f=1MHz,<br>V <sub>AC</sub> =25mV                                                   |      | 6378 |      | pF   |
| C <sub>oss</sub>    | Output Capacitance             |                                                                                                            |      | 245  |      | pF   |
| C <sub>rss</sub>    | Reverse Transfer Capacitance   |                                                                                                            |      | 15   |      | pF   |
| g <sub>fs</sub>     | Transconductance               | V <sub>DS</sub> =20V, I <sub>D</sub> =50A                                                                  |      | 51   |      | S    |
| E <sub>oss</sub>    | Coss Stored Energy             | V <sub>DS</sub> =1000V, f=1MHz                                                                             |      | 141  |      | μJ   |
| E <sub>on</sub>     | Turn-On Energy (Body Diode)    | V <sub>DS</sub> =800V, V <sub>GS</sub> =-5V/20V,<br>I <sub>D</sub> =50A, L=68μH<br>T <sub>J</sub> =150°C   |      | 2.60 |      | mJ   |
| E <sub>off</sub>    | Turn-Off Energy (Body Diode)   |                                                                                                            |      | 0.73 |      | mJ   |
| Q <sub>g</sub>      | Total Gate Charge              | V <sub>DS</sub> =800V, V <sub>GS</sub> =-5V/20V,<br>I <sub>D</sub> =50A                                    |      | 238  |      | nC   |
| Q <sub>gs</sub>     | Gate-source Charge             |                                                                                                            |      | 76.7 |      | nC   |
| Q <sub>gd</sub>     | Gate-Drain Charge              |                                                                                                            |      | 78.3 |      | nC   |
| R <sub>G(int)</sub> | Internal Gate Resistance       | f=1MHz, V <sub>AC</sub> =25mV                                                                              |      | 3.5  |      | Ω    |
| t <sub>d(on)</sub>  | Turn-on Delay Time             | V <sub>DS</sub> =800V, V <sub>GS</sub> =-5V/20V,<br>I <sub>D</sub> =50A, L=68 μH<br>R <sub>ext</sub> =2.5Ω |      | 42   |      | ns   |
| t <sub>r</sub>      | Rise Time                      |                                                                                                            |      | 34   |      | ns   |
| t <sub>d(off)</sub> | Turn-off Delay Time            |                                                                                                            |      | 71   |      | ns   |
| t <sub>f</sub>      | Fall Time                      |                                                                                                            |      | 13   |      | ns   |
| E <sub>AS</sub>     | Avalanche energy, single Pulse | V <sub>DS</sub> =150V, I <sub>D</sub> =30A                                                                 |      | 3500 |      | mJ   |

**Typical Performance-Reverse Diode(T<sub>J</sub> = 25°C unless otherwise specified)**

| Symbol           | Parameter                        | Test Conditions                                                                                                | Min. | Typ. | Max. | Unit |
|------------------|----------------------------------|----------------------------------------------------------------------------------------------------------------|------|------|------|------|
| V <sub>FSD</sub> | Forward Voltage                  | V <sub>GS</sub> =0V, I <sub>F</sub> =37.5A, T <sub>J</sub> =25°C                                               |      | 4.6  | 6    | V    |
|                  |                                  | V <sub>GS</sub> =0V, I <sub>F</sub> =37.5A, T <sub>J</sub> =150°C                                              |      | 4.2  | 6    | V    |
| I <sub>S</sub>   | Continuous Diode Forward Current | V <sub>GS</sub> =0V, T <sub>C</sub> =25°C                                                                      |      | 110  |      | A    |
| t <sub>rr</sub>  | Reverse Recovery Time            | V <sub>GS</sub> =-5 V, I <sub>F</sub> =50 A,<br>V <sub>R</sub> =800 V, di/dt=900A/μs,<br>T <sub>J</sub> =150°C |      | 98   |      | nS   |
| Q <sub>rr</sub>  | Reverse Recovery Charge          |                                                                                                                |      | 613  |      | nC   |
| I <sub>rrm</sub> | Peak Reverse Recovery Current    |                                                                                                                |      | 18   |      | A    |

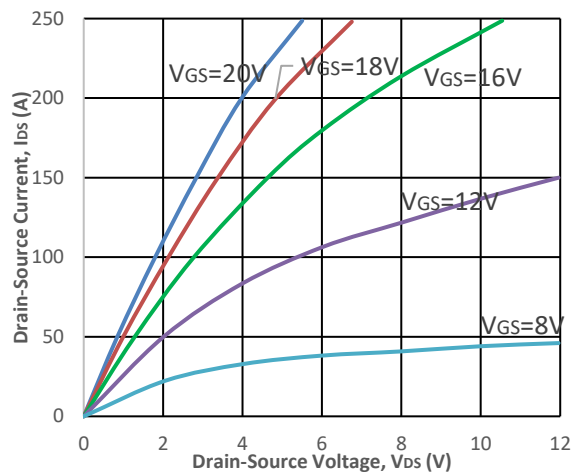
**Thermal Characteristics**

| Symbol                 | Parameter                               | Value. | Unit |
|------------------------|-----------------------------------------|--------|------|
| R <sub>θJC</sub>       | Thermal Resistance, Junction-to-Case    | 0.35   | °C/W |
| R <sub>θJA</sub>       | Thermal Resistance, Junction-to-Ambient | 40     | °C/W |
| V <sub>ISOLATION</sub> | Any terminal to case, t=1 minute        | 2500   | V    |

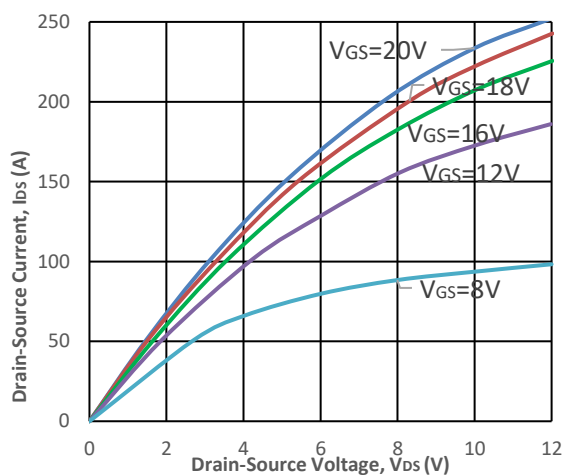
The values are based on the junction-to case thermal impedance which is measured with the device mounted to a large heat sink assuming maximum junction temperature of T<sub>J</sub>(max)=175°C

### Electrical Characteristics

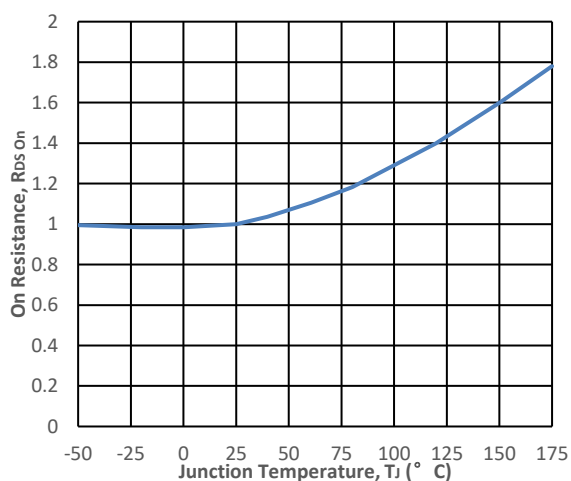
**Fig1. Output characteristics ( $T_J = 25^\circ\text{C}$ )**



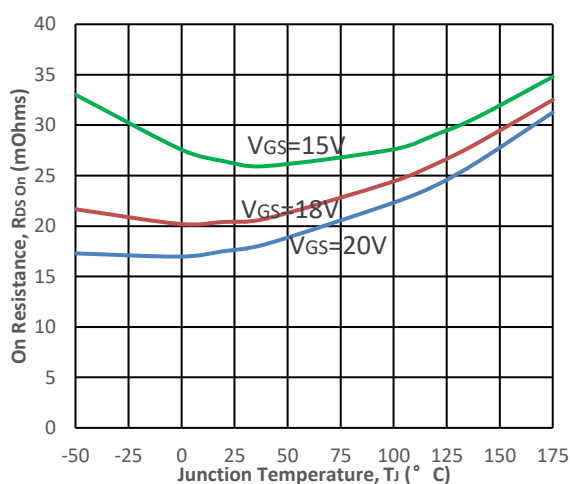
**Fig2. Output characteristics ( $T_J = 150^\circ\text{C}$ )**



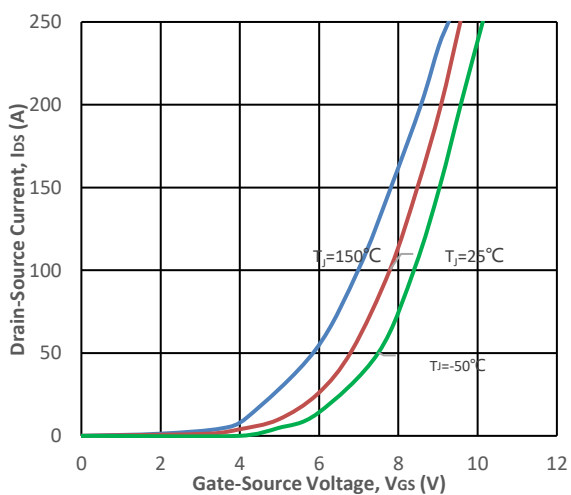
**Fig3. Normalized On-Resistance vs. Temperature**



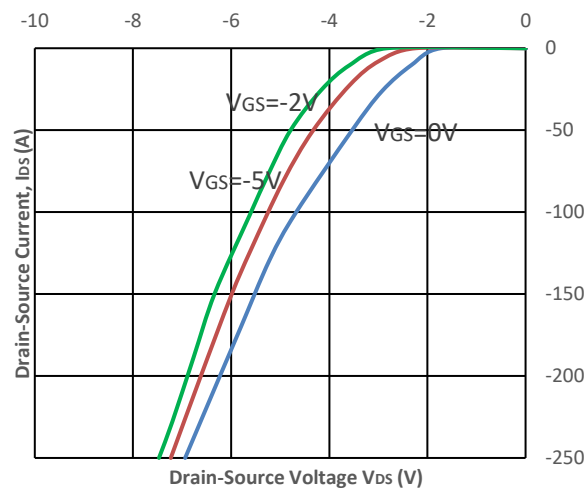
**Fig4. On-Resistance vs. Temperature**



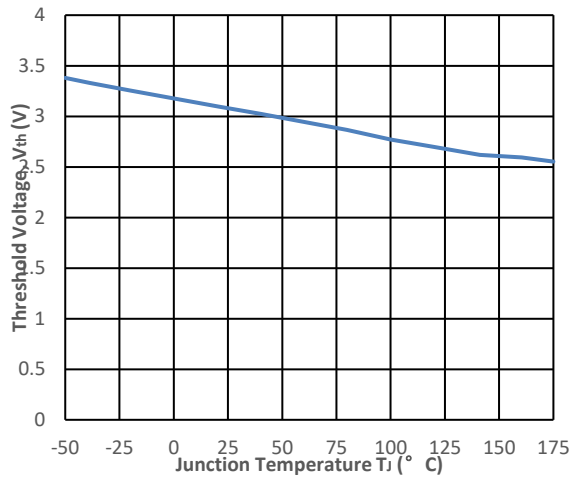
**Fig5. Transfer Characteristic**



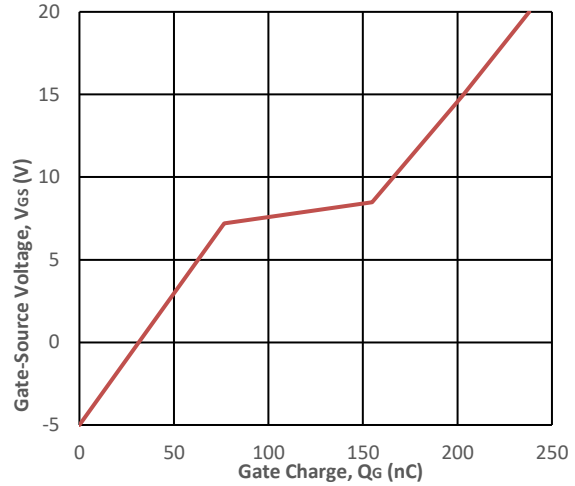
**Fig6. Body Diode Characteristic at  $25^\circ\text{C}$**



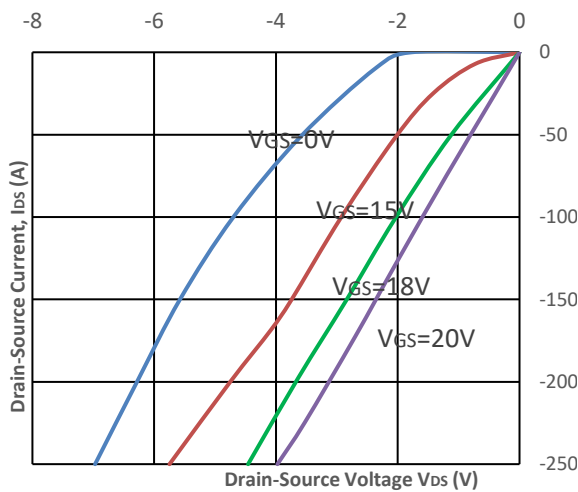
**Fig7. Threshold Voltage vs. Temperature**



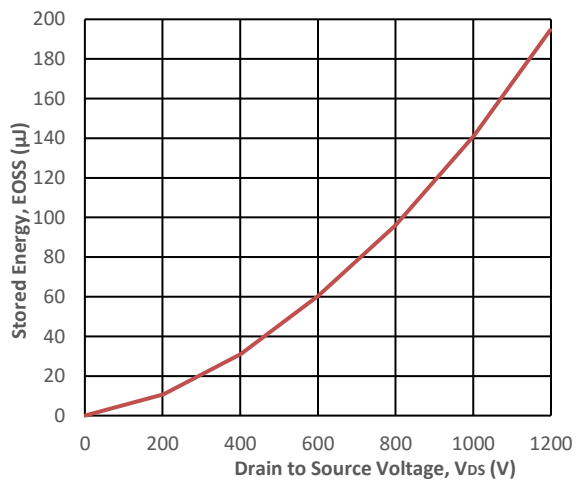
**Fig8. Gate Charge Characteristics**



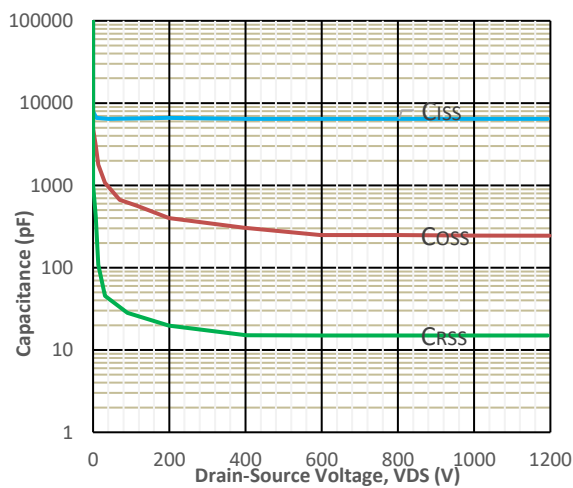
**Fig9. 3rd Quadrant Characteristic at 25  $^{\circ}$  C**



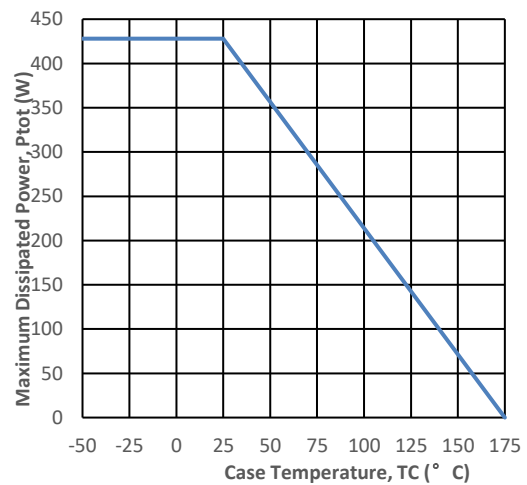
**Fig10. Output Capacitor Stored Energy**



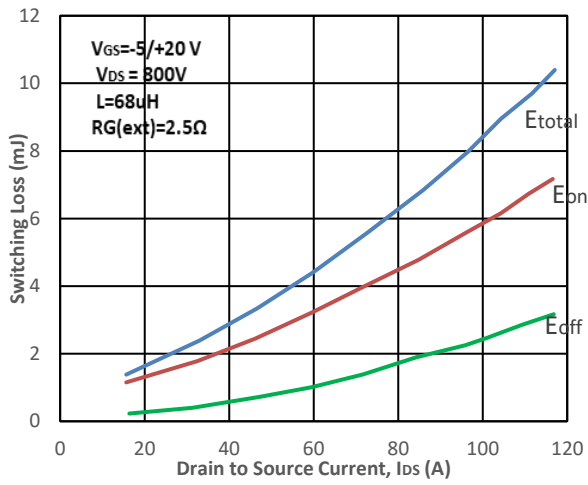
**Fig11. Capacitances vs. Drain-Source**



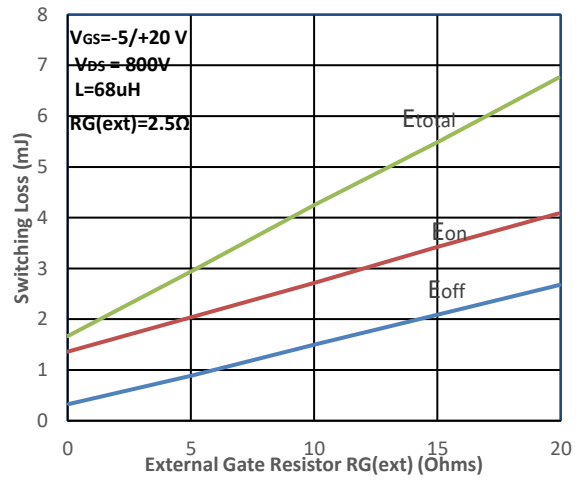
**Fig12. Max Power Dissipation Derating Vs  $T_c$**



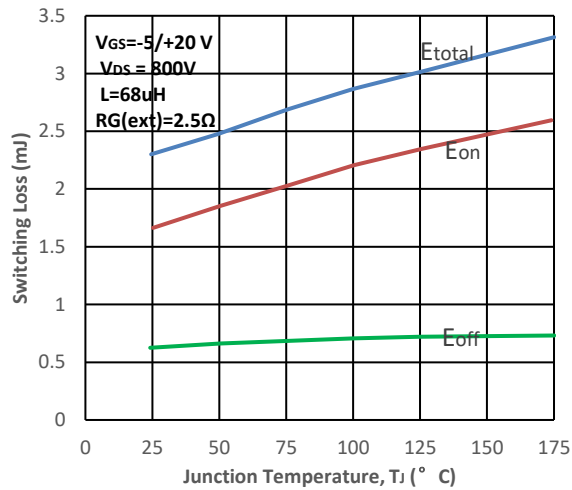
**Fig13. Switching Energy vs. Drain Current**



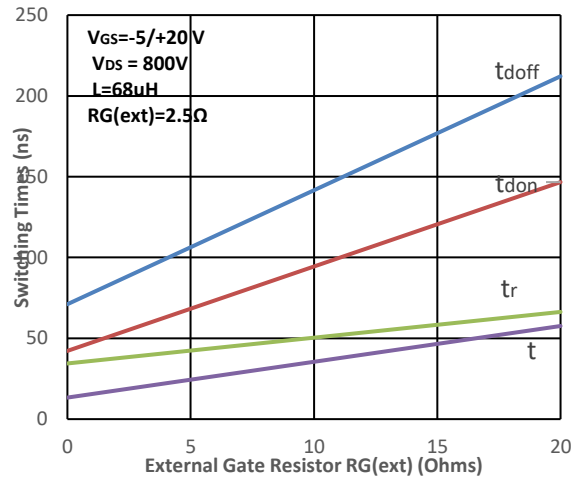
**Fig14. Switching Energy vs.  $R_{G(ext)}$**



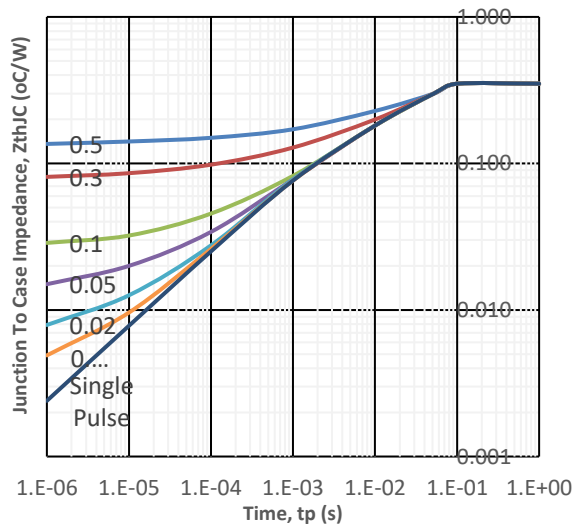
**Fig15. Switching Energy vs. Temperature**



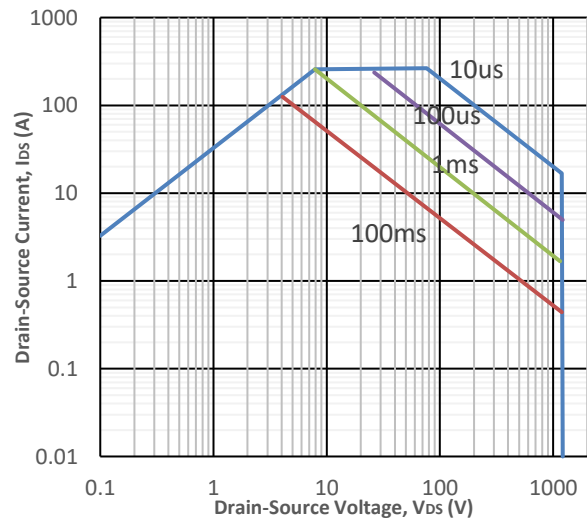
**Fig16. Switching Times vs.  $R_{G(ext)}$**



**Fig17. Transient Thermal Impedance**



**Fig18. Safe Operating Area**



### Package Drawing and Dimensions ( UNIT: mm )

